

## Некоторые публикации Копьева Петра Сергеевича за 2018-2022 годы

1. Slipchenko,S; Shamakhov,V; Nikolaev,D; Fomin,E; Soshnikov,I; Bondarev,A; Mitrofanov,M; Pikhtin,N; Коп`ев,Р

Basics of surface reconstruction during selective area metalorganic chemical vapour-phase epitaxy of GaAs films in the stripe-type ultra-wide window. *Appl. Surf. Sci.*, v.588, 2022, ArtNo: #152991

<http://dx.doi.org/10.1016/j.apsusc.2022.152991>

2. Slipchenko,SO; Podoskin,AA; Veselov,DA; Strelets,VA; Rudova,NA; Pikhtin,NA; Bagaev,TA; Ladugin,MA; Marmalyuk,AA; Коп`ев,PS

Tunnel-Coupled Laser Diode Microarray as a kW-Level 100-ns Pulsed Optical Power Source ( $\lambda=910$  nm). *IEEE Photonics Technol. Lett.*, v.34, 1, 2022, p. 35 - 38

<http://dx.doi.org/10.1109/LPT.2021.3134370>

3. Шашкин,ИС; Лешко,АЮ; Шамахов,ВВ; Романович,ДН; Капитонов,ВА; Бахвалов,КВ; Слипченко,СО; Пихтин,НА; Копьев,ПС

Исследование динамики выходной оптической мощности полупроводниковых лазеров (1070 nm) с маломодовым латеральным волноводом мезаполосковой конструкции при сверхвысоких токах накачки. *Письма ЖТФ*, т.47, 7, 2021, с. 42 - 45

<http://dx.doi.org/10.21883/PJTF.2021.07.50799.18644>

4. Shamakhov,V; Nikolaev,D; Slipchenko,S; Fomin,E; Smirnov,A; Eliseyev,I; Pikhtin,N; Коп`ев,Р

Surface nanostructuring during selective area epitaxy of heterostructures with ingaas qws in the ultra-wide windows. *Nanomaterials*, v.11, 1, 2021, ArtNo: #11

<http://dx.doi.org/10.3390/nano11010011>

5. Slipchenko,SO; Podoskin,AA; Golovin,VS; Pikhtin,NA; Коп`ев,PS

Near-Field Dynamics of Ultra-Wide-Aperture (800  $\mu\text{m}$ ) Diode Lasers Under Nanosecond Pulse Excitation. *IEEE Photonics Technol. Lett.*, v.33, 1, 2021, p. 7 - 10

<http://dx.doi.org/10.1109/LPT.2020.3040063>

6. Danilov,LV; Mikhailova,MP; Ivanov,EV; Yakovlev,YP; Коп`ев,PS

Electroluminescence in Heterostructures GaSb/AlSb/InAsSb Due to Tunneling Mechanism of Radiative Recombination. *Semiconductors*, v.54, 14, 2020, p. 1820 - 1822

<http://dx.doi.org/10.1134/S1063782620140055>

7. Михайлова,МП; Иванов,ЭВ; Данилов,ЛВ; Калинина,КВ; Яковлев,ЮП; Копьев,ПС

Излучательная рекомбинация и ударная ионизация в полупроводниковых наноструктурах (Обзор). *ФТП*, т.54, 12, 2020, с. 1267 - 1288

<http://dx.doi.org/10.21883/FTP.2020.12.50226.9509>

8. Mikhailova,MP; Ivanov,EV; Danilov,LV; Kalinina,KV; Pivovarova,AA; Yakovlev,YP; Коп`ев,PS

Large blue shift of electroluminescence spectrum in nanoheterostructures with a deep AlSb/InAsSb/AlSb quantum well. *J. Appl. Phys.*, v.126, 23, 2019, ArtNo: #235703

<http://dx.doi.org/10.1063/1.5131027>

9. Sedova,IV; Lebedev,MV; Klimko,GV; Sorokin,SV; Solov`ev,VA; Cherkashinin,G; Nappini,S; Magnano,E; Drozdov,MN; Kop`ev,PS; Ivanov,SV  
Coherent InAs/CdSe and InAs/ZnTe/CdSe heterovalent interfaces: Electronic and chemical structure. *Appl. Surf. Sci.*, v.448, 2018, p. 455 - 464  
<http://dx.doi.org/10.1016/j.apsusc.2018.04.113>

10. Komkov,OS; Firsov,DD; Chernov,MYu; Solov`ev,VA; Sitnikova,AA; Kop`ev,PS; Ivanov,SV  
Radiative versus non-radiative recombination in high-efficiency mid-IR InSb/InAs/In(Ga,Al)As/GaAs metamorphic nanoheterostructures. *J. Phys. D-Appl. Phys.*, v.51, 5, 2018, ArtNo: #055106  
<http://dx.doi.org/10.1088/1361-6463/aaa25d>

11. Solov`ev,VA; Chernov,MY; Baidakova,MV; Kirilenko,DA; Yagovkina,MA; Sitnikova,AA; Komissarova,TA; Kop`ev,PS; Ivanov,SV  
Strain relaxation in convex-graded In<sub>x</sub>Al<sub>1-x</sub>As (x=0.05-0.79) metamorphic buffer layers grown by molecular beam epitaxy on GaAs(001). *Superlattices Microstruct.*, v.113, 2018, p. 777 - 784  
<http://dx.doi.org/10.1016/j.spmi.2017.12.018>